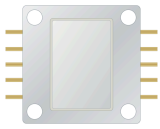
13400–14600 MHz GaN Packaged Power Amplifier — PSAT 44.5 dBm (typical)

LCI-PA-13400-14600-PS44p5T · 13400–14600 MHz · GaN Packaged Power Amplifier.



The RF table specifies: PSAT 44.5 dBm (typical); Power gain 19.5 dB (typical); PAE 32 % (typical). RF test conditions: TA = +25 °C; VDS = 28 V; VGS ∈ [-3.2, -2.4] V; Pin = 25 dBm; CW.

CMW017C

Apply gate bias before drain bias. Remove drain bias before gate bias.

Vg: C = 10 µF

Vg: 1, 5

RFin: 3

Vd: 6, 10

RFout: 8

NC: 2, 4, 7, 9

Package outline dimensions: 15.25 × 15.25 × 1.4 mm.

RF characteristics

TA = +25 °C; VDS = 28 V; VGS ∈ [-3.2, -2.4] V; Pin = 25 dBm; CW

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Operating frequency	f	13400	-	14600	MHz
Saturated output power	-	43.7	44.5	-	dBm
Power gain	-	-	19.5	-	dB
Power-added efficiency	-	28	32	-	%
Power-gain flatness	-	-	-	±0.6	dB
Small-signal gain	S21	-	28	-	dB

DC bias and current

Parameter	Symbol	Minimum	Typical	Maximum	Value	Unit
Drain voltage	-	-	-	-	28	V
Gate voltage	-	-	-	-	[-3.2, -2.4]	V

Absolute limits

Absolute limits; these are not normal operating targets.

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Maximum drain-source voltage	-	-	-	32	V
Minimum gate bias	-	-5	-	-	V
Storage temperature	-	-65	-	150	°C
Maximum input power	-	-	-	28	dBm

Package outline dimensions

Parameter	Value	Unit
Package outline dimensions	15.25 × 15.25 × 1.4	mm

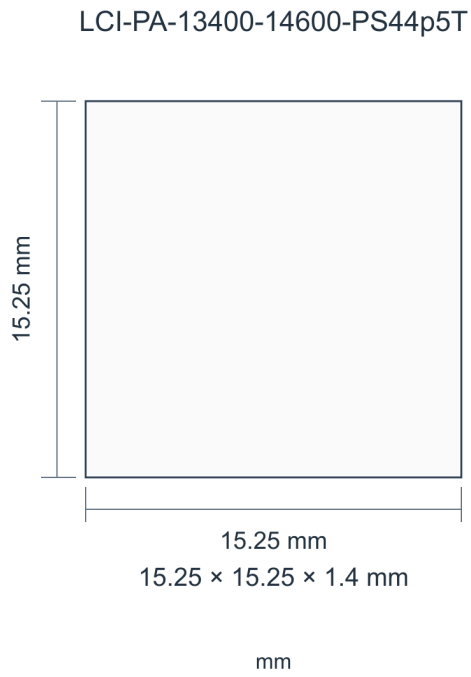
Current publication record · 1.8 · 2026-11-12. Product description or editorial content updated. Replaces revision 1.7.

Integration notes

CMW017C Apply gate bias before drain bias. Remove drain bias before gate bias. Vg: C = 10 µF Vg: 1, 5 RFin: 3 Vd: 6, 10 RFout: 8 NC: 2, 4, 7, 9

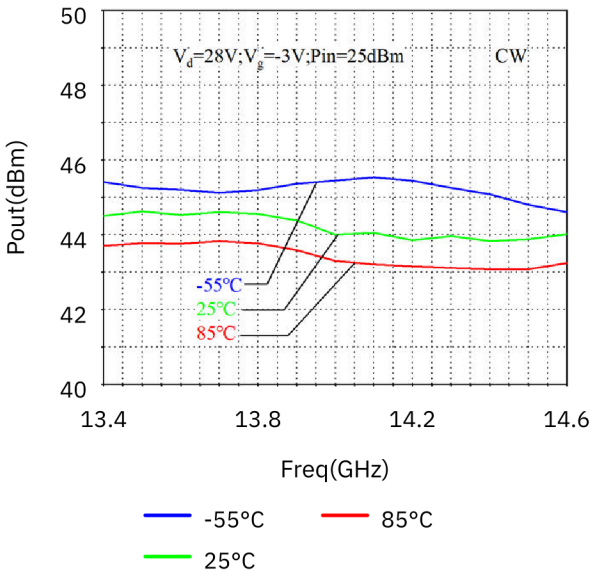
Mechanical Outline

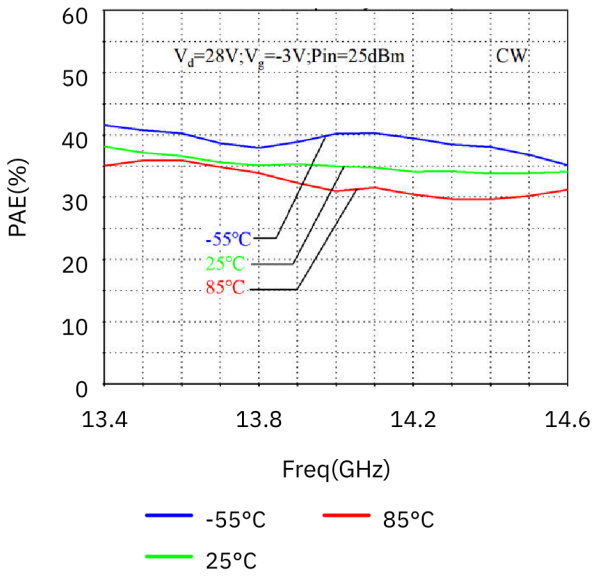
Partial drawing showing confirmed dimensions in mm. Use the complete installation drawing for installation.

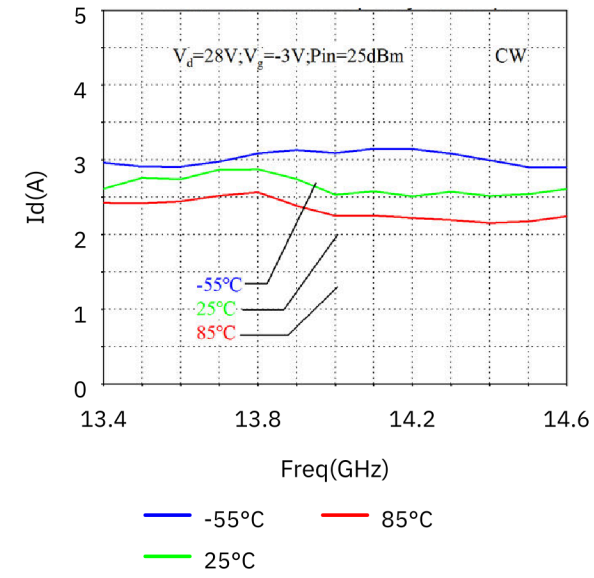


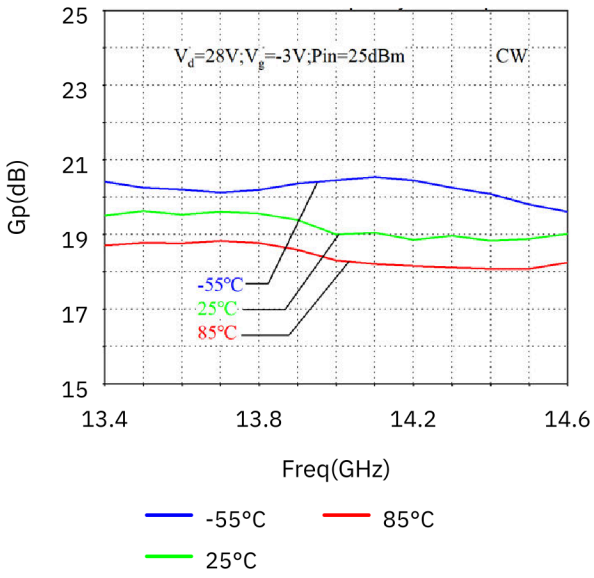
Performance curves

Each performance plot applies to its stated operating conditions.

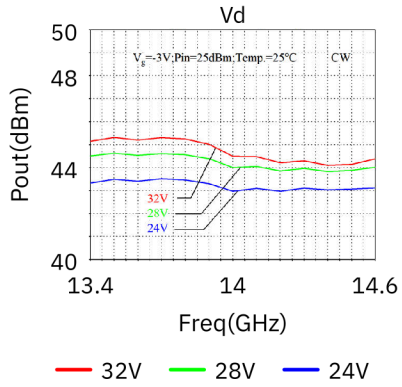


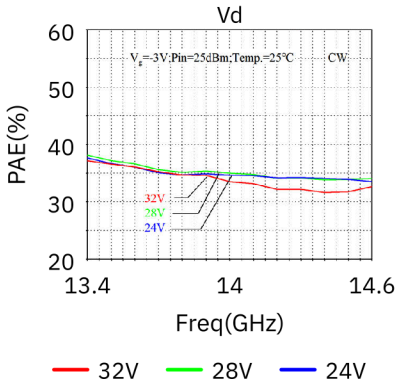


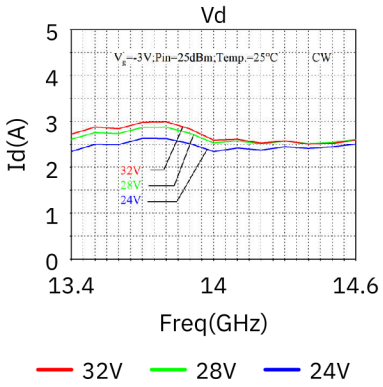


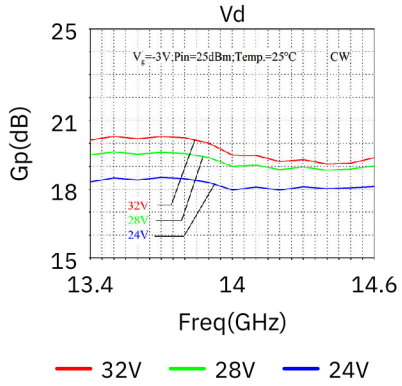


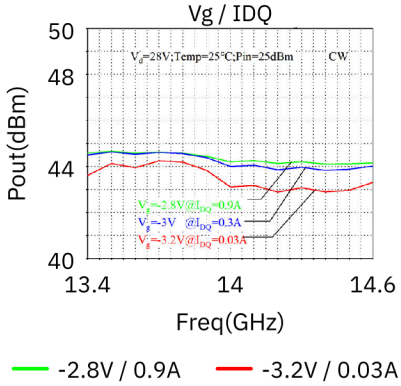
Output power; Power-added efficiency; Drain current; Power gain. Vd = 28 V; Vg = -3 V; Pin = 25 dBm; CW; T = -55/25/85 °C.

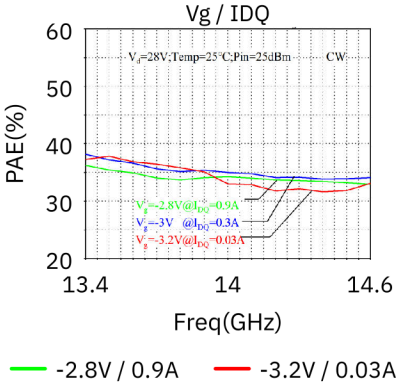


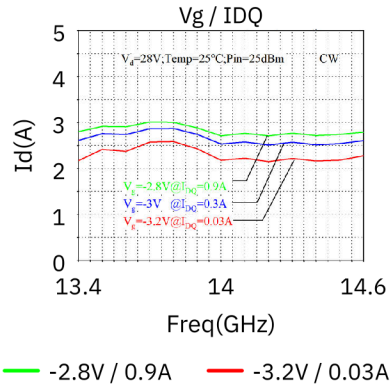


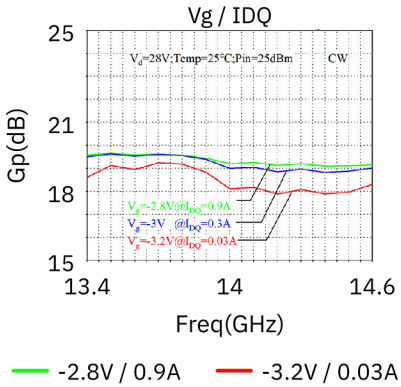




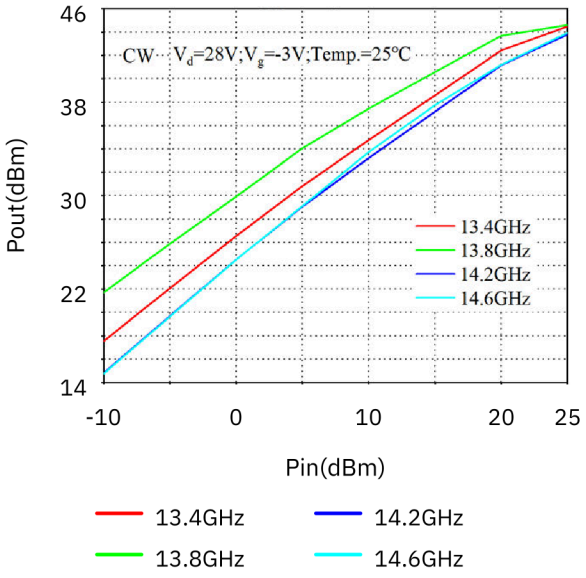


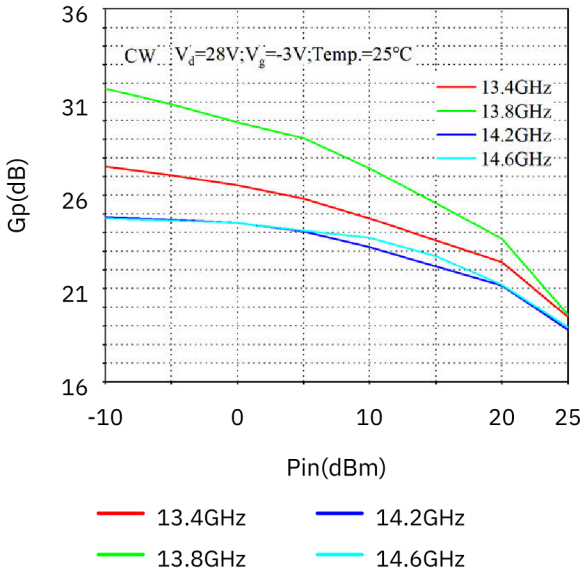


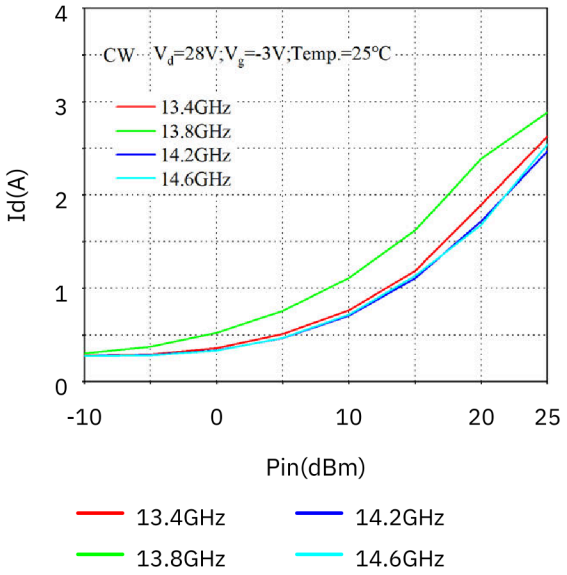




Output power; Power-added efficiency; Drain current; Power gain. CW; TA = 25 °C; Pin = 25 dBm. Plots 1–4: Vg = -3 V; Vd = 32/28/24 V. Plots 5–8: Vd = 28 V; Vg = -2.8 V/IDQ = 0.9 A, -3 V/IDQ = 0.3 A, -3.2 V/IDQ = 0.03 A. Power gain Gp is expressed in dB.







Pout(dBm); Gp(dB); Id(A). CW; Vd = 28 V; Vg = -3 V; TA = 25 °C; Pin = -10...25 dBm; f = 13.4/13.8/14.2/14.6 GHz.

Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.